T Mumban	ロ·+c	Search Toyt	DB	Time stamp
L Number	Hits	Search Text		2004/01/12 08:08
-	348	(438/15).CCLS.	USPAT	1
-	258	(438/113).CCLS.	USPAT	2002/07/03 08:58
-	94	(438/110).CCLS.	USPAT	2002/07/03 08:58
i	59	(438/114).CCLS.	USPAT	2002/07/03 08:58
l_	681	438/15,110,113,114.ccls.	USPAT	2002/12/19 14:38
_			USPAT	2001/08/07 15:09
-	401	438/15,110,113,114.ccls. and test\$3	i e	
-	272	(438/15,110,113,114.ccls. and test\$3) and	USPAT	2001/08/07 15:10
		(dice\$4 or cut\$5)		
-	901	438/15,110,113,114.ccls.	USPAT;	2002/02/04 09:53
			EPO; JPO;	
			DERWENT	
	4.60	420/15 410 412 414 3 1 4 422	l .	0000/00/04 00.54
-	460	438/15,110,113,114.ccls. and test\$3	USPAT;	2002/02/04 09:54
			EPO; JPO;	!
İ			DERWENT	
-	325	(438/15,110,113,114.ccls. and test\$3) and	USPAT;	2002/02/05 08:26
	020	(dic\$5 or cut\$5)	EPO; JPO;	
		(dicys of cutys)		
1	_		DERWENT	0000/20/20
-	5		USPAT	2003/10/24 12:32
į		or ("6309909") or ("6326697")).PN.		
_	7	, , , , , , , , , , , , , , , , , , , ,	USPAT	2002/02/05 09:49
ì	i '	or ("6309909") or ("6326697") or	1	
		("5858815") or ("5137836")).PN.		0000/00/05 55 55
-	326		USPAT;	2002/02/05 08:28
		(dic\$5 or cut\$5)	EPO; JPO;	
			DERWENT	
_	. 0	((438/15,110,113,114.ccls. and test\$3) and	USPAT;	2002/02/05 08:33
	0			2002/02/03 00:33
		(dic\$5 or cut\$5)) and (magnet\$7 adj	EPO; JPO;	
		align\$5)	DERWENT	
	170	((438/15,110,113,114.ccls. and test\$3) and	USPAT;	2002/02/05 08:32
		(dic\$5 or cut\$5)) and (align\$5)	EPO; JPO;	
		, , ,	DERWENT	
_	2705	magnet\$7 adj align\$5	USPAT;	2002/02/05 08:56
-	2703	magnety/ adj arrynys		2002/02/03 00.36
			EPO; JPO;	
			DERWENT	
-	0	((USPAT;	2002/02/05 08:37
		dielectric adj tape)	EPO; JPO;	
		* * *	DERWENT	
_	_	wafer adj20 dielectric adj tape	USPAT;	2002/02/05 08:37
-		warer adjag dretectiff adj tape		2002/02/03 00:3/
			EPO; JPO;	
			DERWENT	
-	0	wafer adj dielectric adj tape	USPAT;	2002/02/05 08:38
			EPO; JPO;	
			DERWENT	
_	248	(magnet\$7 adj align\$5) and semiconductor	USPAT;	2002/02/05 08:57
	240	(magnety, adj arrgnys) and semiconductor		2002/02/03 00.3/
			EPO; JPO;	
		l	DERWENT	,
-	0	((magnet\$7 adj align\$5) and ring) and	USPAT;	2002/02/05 08:49
		(charged adj slot)	EPO; JPO;	
			DERWENT	
_	0	(magnet\$7 adj align\$5) and (charged adj	USPAT;	2002/02/05 08:49
				2002/02/03 00.49
		slot)	EPO; JPO;]
			DERWENT	
	613	(magnet\$7 adj align\$5) and ring	USPAT;	2002/02/05 08:50
			EPO; JPO;	
			DERWENT	
_	47	((magnot\$7 add align\$5) and wing) and	ſ	2002/02/05 00-51
-	4/	((magnet\$7 adj align\$5) and ring) and	USPAT;	2002/02/05 08:51
		semiconductor	EPO; JPO;	
			DERWENT	
-	3066	optically adj align\$5	USPAT;	2002/02/05 08:56
			EPO; JPO;	
			DERWENT	
	C10	/onticelly add elign(E) and assistant		2002/02/05 00:57
-	612	(optically adj align\$5) and semiconductor	USPAT;	2002/02/05 08:57
			EPO; JPO;	
			DERWENT	
_	8	(("6077757") or ("6335224") or ("6309943")	USPAT	2003/06/02 08:10
		or ("6309909") or ("6326697") or		
1		("5858815") or ("5137836") or		1
L		("4781969")).PN.	<u> </u>	

_	10260	wood.inv.	USPAT;	2002/07/03 08:13
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	520		IBM TDB	2002/07/03 08:13
-	539	wood.inv. and alan	USPĀT;	2002/07/03 08:13
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	1
	0.00		IBM_TDB	2222 (27 (22 22 14
-	232	(wood.inv. and alan) and (micron adj	USPAT;	2002/07/03 08:14
		technology)	US-PGPUB;	
			EPO; JPO;	
İ			DERWENT;	
	1	/# CO CO CE O #) - PN 7	IBM_TDB	2002/12/20 12:04
-	1	("6268650").PN.	USPAT	2002/12/20 10:24
-	425	(438/15).CCLS.	USPAT	2002/07/08 08:43
-	331	(438/113).CCLS.	USPAT	2002/07/08 08:57
-	140	(438/110).CCLS.	USPAT	2002/07/08 08:57
-	90	(438/114).CCLS.	USPAT	2002/07/08 08:57
ļ -	425	l :	USPAT	2002/07/08 08:43
-	331		USPAT	2002/07/08 08:57
-	140	(438/110).CCLS.	USPAT	2002/07/08 08:57
-	90	(438/114).CCLS.	USPAT	2002/07/08 14:32
-	13	(("6389689") or ("5977629") or ("5796170")	USPAT	2002/07/08 10:35
		or ("6326700") or ("6268650") or		
		("5858815") or ("5817535") or ("5770032")		
		or ("4781969") or ("5073840") or		
		("5696033") or ("5834839") or		
1		("6160714")).PN.	·	
-	8	(("6309909") or ("5858815") or ("5137836")	USPAT	2002/07/09 09:56
		or ("6077757") or ("6326697") or		
		("6165885") or ("5834320") or		
		("4781969")).PN.		
-	0	(wafer adj (bond\$3 or attach\$3) near4	USPAT;	2002/12/19 15:00
		(dielectric adj (layer or film))) same	US-PGPUB;	
		test\$3 same (cut\$4 or dic\$3 or separat\$3)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	1
-	0	(wafer adj (bond\$3 or attach\$3) near4	USPAT;	2002/12/19 14:07
		(dielectric adj (layer or film))) same	US-PGPUB;	
		test\$3 same (cut\$4 or dic\$3 or separat\$3)	EPO; JPO;	
			DERWENT;	
			IBM_TDB -	
_	19		USPAT;	2002/12/19 14:07
		(dielectric adj (layer or film))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	0000/10/15
_	0	(wafer adj (bond\$3 or attach\$3) near4	USPAT;	2002/12/19 14:38
		(dielectric adj (layer or film))) same	US-PGPUB;	
	1	test\$3	EPO; JPO;	
			DERWENT;	
		1,20/15 110 110 111	IBM_TDB	0000 (00 (00 00 00 00 00 00 00 00 00 00
_	963	l · · · · · · · · · · · · · · · · · · ·	USPAT	2002/12/19 14:38
-	1212	438/15,110,113,114.ccls.	USPAT;	2002/12/19 14:38
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
,		100/15 110 110 111	IBM_TDB	0000 400 400
-	0	438/15,110,113,114.ccls. and ((wafer adj	USPAT;	2002/12/19 14:40
		(bond\$3 or attach\$3) near4 (dielectric adj	US-PGPUB;	
		(layer or film))) same test\$3)	EPO; JPO;	
	1		DERWENT;	
	[_]		IBM_TDB	0000/12/22
-	9	(wafer adj (dielectric adj (layer or	USPAT;	2002/12/20 08:18
		film))) same test\$3	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
L	L		IBM_TDB	

-	13	(("5834839") or ("6389689") or ("6160714") or ("5977629") or ("6326700") or	USPAT	2002/12/19 15:19
		("6268650") or ("5858815") or ("5817535")		
		or ("5770032") or ("5796170") or		
		("4781969") or ("5073840") or		
	0.5	("5696033")).PN.	USPAT;	2002/12/20 08:42
_	85	wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)	US-PGPUB;	2002/12/20 08:42
		(cutys of dicys of sileys)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	78	(wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)) and	USPAT; US-PGPUB;	2002/12/20 09:38
1		semiconductor	EPO; JPO;	
	İ		DERWENT;	
			IBM_TDB	0000/10/00 00 05
_	348	<pre>(wafer same (dielectric adj (layer or film))) same test\$3</pre>	USPAT; US-PGPUB;	2002/12/20 09:35
		IIIM) / Same Cescys	EPO; JPO;	
			DERWENT;	:
ļ		<u>.</u>	IBM_TDB	
-	322	((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor	USPAT; US-PGPUB;	2002/12/20 09:38
		IIIm/// Same testss / and semiconductor	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
[-	98	<pre>((((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor)</pre>	USPAT; US-PGPUB;	2002/12/20 09:39
		and (cut\$3 or dic\$3)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1		USPAT	2002/12/20 10:24 2002/12/23 11:53
-	3	(("5897337") or ("5858815") or ("6389689")).PN.	USPAT	2002/12/23 11:53
_	2	(("5897337") or ("6389689")).PN.	USPAT	2002/12/23 11:53
-	9187		USPAT;	2003/05/20 07:59
		semiconductor	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	4418		USPAT;	2003/05/20 08:02
		and semiconductor) and (dic\$4 or cut\$4 or separat\$5)	US-PGPUB; EPO; JPO;	
		separaty)	DERWENT;	
			IBM TDB	
-	4476	(((balls adj grid adj arrays) or (BGA))	USPAT;	2003/05/20 08:04
		and semiconductor) and (dic\$4 or cut\$4 or separat\$5 or saw\$4)	US-PGPUB; EPO; JPO;	
		departe of banys,	DERWENT;	
			IBM_TDB	
-	955		USPAT;	2003/05/20 08:04
		and semiconductor) and (dic\$4 or cut\$4 or separat\$5)) and (metal adj (film or	US-PGPUB; EPO; JPO;	
		layer))	DERWENT;	
			IBM_TDB	
-	970	((((balls adj grid adj arrays) or (BGA))	USPAT;	2003/05/20 08:04
		and semiconductor) and (dic\$4 or cut\$4 or separat\$5 or saw\$4)) and (metal adj (film	US-PGPUB; EPO; JPO;	
		or layer))	DERWENT;	
		(#2004.005.0.54.0.#). ===	IBM_TDB	0000/05/05
_	1 472	("20010052642").PN. wafer and (metal adj (film or layer)) and	US-PGPUB USPAT;	2003/05/20 08:12 2003/05/20 08:52
_	4 /2	(attach\$5 or bond\$4) and ((balls adj grid	US-PGPUB;	2003/03/20 00:52
		adj arrays) or (BGA)) and semiconductor	EPO; JPO;	
		and (dic\$4 or cut\$4 or separat\$5)	DERWENT;	
_	233	(wafer and (metal add (film or lawer)) and	IBM_TDB USPAT;	2004/01/12 08:09
_	233	(wafer and (metal adj (film or layer)) and (attach\$5 or bond\$4) and ((balls adj grid	US-PGPUB;	2004/01/12 00:09
		adj arrays) or (BGA)) and semiconductor	EPO; JPO;	
		and (dic\$4 or cut\$4 or separat\$5)) and	DERWENT;	
		@ad<=20000616	IBM_TDB	

			T =====	0000/05/05
_	212	((wafer and (metal adj (film or layer))	USPAT;	2003/05/21 08:23
	-	and (attach\$5 or bond\$4) and ((balls adj	US-PGPUB;	
		grid adj arrays) or (BGA)) and	EPO; JPO;	
		semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) and @ad<=20000616) and (dic\$5	IBM_TDB	
		or cut\$6 or saw\$5)		1
-	206		USPAT;	2003/05/20 09:06
		and (attach\$5 or bond\$4) and ((balls adj	US-PGPUB;	
		grid adj arrays) or (BGA)) and	EPO; JPO;	
İ		semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) and @ad<=20000616) and (dic\$5	IBM_TDB	
		or cut\$6)	_	
-	1	(((wafer adj semiconductor) same (metal	USPAT;	2003/05/20 10:06
		adj (film or layer)) same (attach\$5 or	US-PGPUB;	
		bond\$4) same ((balls adj grid adj arrays)	EPO; JPO;	
		or (BGA)) same (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) same (dic\$5 or cut\$6 or	IBM TDB	
		saw\$5)) and @ad<=20000616	_	
-	212		USPAT;	2003/05/21 09:00
		and (attach\$5 or bond\$4) and ((balls adj	US-PGPUB;	
		grid adi arrays) or (BGA)) and	EPO: JPO:	!
İ		semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) and @ad<=20000616) and (dic\$5	IBM TDB	
		or cut\$6 or saw\$5)		
-	172		USPAT;	2003/05/21 09:24
		and (attach\$5 or bond\$4) and ((balls adj	US-PGPUB;	
		grid adj arrays) or (BGA)) and	EPO; JPO;	
	1	semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) and @ad<=20000616) and (dic\$5	IBM TDB	
		or cut\$6 or saw\$5)) and dic\$5		
_	92		USPAT;	2003/05/21 09:35
	1	and (attach\$5 or bond\$4) and ((balls adj	US-PGPUB;	
	1	grid adj arrays) or (BGA)) and	EPO; JPO;	
		semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) and @ad<=20000616) and (dic\$5	IBM TDB	
		or cut\$6 or saw\$5)) and (dicing or diced)	IDM_IDD	
	70		USPAT;	2003/05/21 09:36
-	, , ,		· ·	2003/03/21 09.30
		and (attach\$5 or bond\$4) and ((balls adj	US-PGPUB;	
	1	grid adj arrays) or (BGA)) and semiconductor and (dic\$4 or cut\$4 or	EPO; JPO; DERWENT;	
		separat\$5)) and @ad<=20000616) and (dic\$5	IBM_TDB	
		or cut\$6 or saw\$5)) and (dicing or		
		diced)) and (individual\$3 or each)	HODAM.	2002/05/21 22 22
-	70	((((wafer and (metal adj (film or layer))	USPAT;	2003/05/21 09:36
		and (attach\$5 or bond\$4) and ((balls adj	US-PGPUB;	
		grid adj arrays) or (BGA)) and	EPO; JPO;	
		semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) and @ad<=20000616) and (dic\$5	IBM_TDB	
		or cut\$6 or saw\$5)) and (dicing or		
	_	diced)) and (individual\$3)		
-	6	, , , , , , , , , , , , , , , , , , ,	USPAT;	2003/05/21 09:37
		and (attach\$5 or bond\$4) and ((balls adj	US-PGPUB;	
		grid adj arrays) or (BGA)) and	EPO; JPO;	
		semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) and @ad<=20000616) and (dic\$5	IBM_TDB	
		or cut\$6 or saw\$5)) and (dicing or		
1		diced)) and (individual\$3 adj device)		
i -	2	(("6344401") or ("6566745")).PN.	USPAT	2004/01/12 07:56
-	241	(wafer and (metal adj (film or layer)) and	USPAT;	2004/01/12 08:10
İ		(attach\$5 or bond\$4) and ((balls adj grid	US-PGPUB;	
		adj arrays) or ("BGA")) and semiconductor	EPO; JPO;	
		and (dic\$4 or cut\$4 or separat\$5)) and	DERWENT;	
		@ad<=20000616	IBM TDB	
_	1	l	USPAT;	2003/10/23 10:36
	_	same (attach\$5 or bond\$4) same ((balls adj	US-PGPUB;	
1	1	grid adj arrays) or ("BGA")) same	EPO; JPO;	
		semiconductor same (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5))) and @ad<=20000616	IBM TDB	
1 _	2	(("6153448") or ("20020011859")).PN.	USPAT;	2003/10/24 12:35
1		\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	US-PGPUB	-555, -57, -5
	L	l	20 10100	<u></u>

-	4	(("6153448") or ("20020011859") or	USPAT;	2003/10/24 14:07
		("6064217") or ("5475317")).PN.	US-PGPUB	
-	3	(("6344401") or ("6165885") or	USPAT	2004/01/12 09:14
		("5834320")).PN.		
_	244	(wafer and (metal adj (film or layer)) and	USPAT;	2004/01/12 08:03
		(attach\$5 or bond\$4) and ((balls adj grid	US-PGPUB;	
		adj arrays) or (BGA)) and semiconductor	EPO; JPO;	
		and (dic\$4 or cut\$4 or separat\$5)) and	DERWENT;	
		@ad<=20000616	IBM_TDB	
_	244	(wafer and (metal adj (film or layer)) and	USPAT;	2004/01/12 08:04
		(attach\$5 or bond\$4) and ((balls adj grid	US-PGPUB;	
		adj arrays) or (BGA)) and semiconductor	EPO; JPO;	
İ		and (dic\$4 or cut\$4 or separat\$5)) and	DERWENT;	
		@ad<=20000616	IBM_TDB	
_	166	((wafer and (metal adj (film or layer))	USPAT;	2004/01/12 08:05
		and (attach\$5 or bond\$4) and ((balls adj	US-PGPUB;	
		grid adj arrays) or (BGA)) and	EPO; JPO;	
		semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
j		separat\$5)) and @ad<=20000616) and	IBM_TDB	
		align\$6		
_	688	(438/455).CCLS.	USPAT;	2004/01/12 08:08
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	12	,,,,,,,,		2004/01/12 08:11
		and (wafer and (metal adj (film or layer))	US-PGPUB;	
		and (attach\$5 or bond\$4) and ((balls adj	EPO; JPO;	
		grid adj arrays) or ("BGA")) and (dic\$4 or	DERWENT;	
		cut\$4 or separat\$5)) and @ad<=20000616	IBM_TDB	
-	97	438/\$.ccls. and (wafer and (metal adj	USPAT;	2004/01/12 08:52
İ		(film or layer)) and (attach\$5 or bond\$4)	US-PGPUB;	
		and ((balls adj grid adj arrays) or	EPO; JPO;	
		("BGA")) and (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) and @ad<=20000616	IBM TDB	